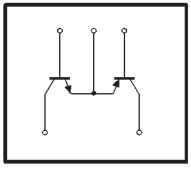
# General purpose (dual transistors)

## FMY5

●**Features**

1) Both the 2SA1514K and 2SC3906K chips in an SMT package.
2) PNP and NPN chips are connected in a common emitter configuration.

●**Circuit diagram**



●**Absolute maximum ratings** (**Ta=25℃**)

| Parameter | Symbol | Limits | Unit | |
|---|---|---|---|---|
| Collector-base voltage | $V_{CBO}$ | 120 | V | |
| Collector-emitter voltage | $V_{CEO}$ | 120 | V | |
| Emitter-base voltage | $V_{EBO}$ | 5 | V | |
| Collector current | $I_C$ | 50 | mA | |
| Power dissipation | $P_C$ | 300 (TOTAL) | mW | * |
| Junction temperature | Tj | 150 | ℃ | |
| Storage temperature | Tstg | −55～+150 | ℃ | |

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●**Package, marking, and packaging specifications**

| Part No. | FMY5 |
|---|---|
| Package | SMT5 |
| Marking | Y5 |
| Code | T148 |
| Basic ordering unit (pieces) | 3000 |

●**Electrical characteristics** (**Ta=25℃**)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|---|---|---|---|---|---|
| Collector-base breakdown voltage | $BV_{CBO}$ | 120 | — | — | V | $I_C$=50/−50 μA |
| Collector-emitter breakdown voltage | $BV_{CEO}$ | 120 | — | — | V | $I_C$=1/−1mA |
| Emitter-base breakdown voltage | $BV_{EBO}$ | 5 | — | — | V | $I_E$=50/−50 μA |
| Collector cutoff current | $I_{CBO}$ | — | — | 0.5 | μA | $V_{CB}$=100/−100V |
| Emitter cutoff current | $I_{EBO}$ | — | — | 0.5 | μA | $V_{EB}$=4/−4V |
| DC current transfer ratio | $h_{FE}$ | 120 | — | 820 | — | $V_{CE}$=6/−6V, $I_C$=2/−2mA |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | — | — | 0.5 | V | $I_C$=10/−10mA, $I_B$=1/−0.1mA |
| Transition frequency | $f_T$ | — | 140 | — | MHz | $V_{CE}$=12/−12V, $I_E$=2/−2mA, f=100MHz * |
| Output capacitance | Cob | — | 3/4 | — | pF | $V_{CB}$=12/−12V, $I_E$=0A, f=1MHz |

Note:The slash denotes NPN/PNP. PNP type negative symbols have been omitted. *Transition frequency of the device.

(94S-440-AC41)

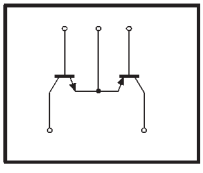
# Totempoles (dual transistors)

## FMY6

●**Features**

1) Both the 2SA1036K and 2SC2411K chips in an SMT package.
2) PNP and NPN chips are connected in a common emitter configuration.
3) High $I_{Cmax.}$ (Max. 500mA)

●**Circuit diagram**



●**Absolute maximum ratings** (**Ta=25℃**)

| Parameter | Symbol | Limits | Unit | |
|---|---|---|---|---|
| Collector-base voltage | $V_{CBO}$ | 40 | V | |
| Collector-emitter voltage | $V_{CEO}$ | 32 | V | |
| Emitter-base voltage | $V_{EBO}$ | 5 | V | |
| Collector current | $I_C$ | 500 | mA | |
| Power dissipation | Pd | 300 (TOTAL) | mW | * |
| Junction temperature | Tj | 150 | ℃ | |
| Storage temperature | Tstg | −55～+150 | ℃ | |

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●**Package, marking, and packaging specifications**

| Part No. | FMY6 |
|---|---|
| Package | SMT5 |
| Marking | Y6 |
| Code | T148 |
| Basic ordering unit (pieces) | 3000 |

●**Electrical characteristics** (**Ta=25℃**)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|---|---|---|---|---|---|
| Collector-base breakdown voltage | $BV_{CBO}$ | 40 | — | — | V | $I_C$=100/−100 μA |
| Collector-emitter breakdown voltage | $BV_{CEO}$ | 32 | — | — | V | $I_C$=1/−1mA |
| Emitter-base breakdown voltage | $BV_{EBO}$ | 5 | — | — | V | $I_E$=100/−100 μA |
| Collector cutoff current | $I_{CBO}$ | — | — | 1 | μA | $V_{CB}$=20/−20V |
| Emitter cutoff current | $I_{EBO}$ | — | — | 1 | μA | $V_{EB}$=4/−4V |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | — | — | 0.4 | V | $I_C$=100/−100mA, $I_B$=10/−10mA |
| DC current transfer ratio | $h_{FE}$ | 120 | — | — | — | $V_{CE}$/$I_C$=3/−3V, $I_C$=10/−10mA |
| Transition frequency | $f_T$ | — | 250/200 | — | MHz | $V_{CE}$=5/−5V, $I_E$=20/−20mA, f=200MHz * |
| Output capacitance | Cob | — | 6.5/7 | — | pF | $V_{CE}$=10/−10V, $I_E$=0A, f=1MHz |

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. *Transition frequency of mounted transistor.

(96-438-BD11)

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